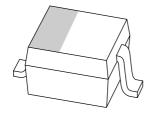
# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# **PMEG2010EA**Low V<sub>F</sub> (MEGA) Schottky barrier diode

Product data sheet Supersedes data of 2002 Dec 10 2004 Feb 06



# Low V<sub>F</sub> (MEGA) Schottky barrier diode

# PMEG2010EA

#### **FEATURES**

Forward current: 1 AReverse voltage: 20 V

• Ultra high-speed switching

· Very low forward voltage

• Very small plastic SMD package.

#### **APPLICATIONS**

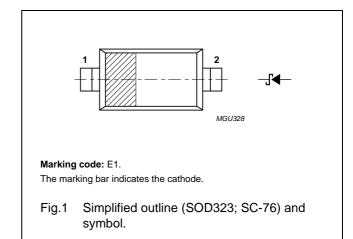
- Ultra high-speed switching
- · Voltage clamping
- · Protection circuits.

# **DESCRIPTION**

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a SOD323 (SC-76) very small SMD plastic package.

#### **PINNING**

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | cathode     |
| 2   | anode       |



# **ORDERING INFORMATION**

| TYPE       | PACKAGE |  |         |  |
|------------|---------|--|---------|--|
| NUMBER     | NAME    | DESCRIPTION                              | VERSION |  |
| PMEG2010EA | _       | plastic surface mounted package; 2 leads | SOD323  |  |

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                           | CONDITIONS   | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|--|------|------|------|
| V <sub>R</sub>   | continuous reverse voltage          |  | _    | 20   | V    |
| I <sub>F</sub>   | continuous forward current          |  | _    | 1    | Α    |
| I <sub>FSM</sub> | non-repetitive peak forward current | t <sub>p</sub> = 8.3 ms half sinewave;<br>JEDEC method | _    | 5    | А    |
| T <sub>stg</sub> | storage temperature                 |  | -65  | +150 | °C   |
| T <sub>j</sub>   | junction temperature                |  | _    | 125  | °C   |
| T <sub>amb</sub> | operating ambient temperature       |  | -65  | +125 | °C   |

# Low V<sub>F</sub> (MEGA) Schottky barrier diode

PMEG2010EA

# **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

| SYMBOL         | PARAMETER                  | CONDITIONS                                 | TYP. | MAX. | UNIT |
|----------------|----------------------------|--|------|------|------|
| V <sub>F</sub> | continuous forward voltage | see Fig.2; note 1                          |      |      |      |
|                |                            | I <sub>F</sub> = 10 mA                     | 240  | 270  | mV   |
|                |                            | I <sub>F</sub> = 100 mA                    | 300  | 350  | mV   |
|                |                            | I <sub>F</sub> = 1000 mA                   | 480  | 550  | mV   |
| I <sub>R</sub> | continuous reverse current | see Fig.3; note 1                          |      |      |      |
|                |                            | V <sub>R</sub> = 5 V                       | 5    | 10   | μΑ   |
|                |                            | V <sub>R</sub> = 8 V                       | 7    | 20   | μΑ   |
|                |                            | V <sub>R</sub> = 15 V                      | 10   | 50   | μΑ   |
| C <sub>d</sub> | diode capacitance          | $V_R = 5 \text{ V}$ ; f = 1 MHz; see Fig.4 | 19   | 25   | pF   |

# Note

1. Pulsed test:  $t_p$  = 300  $\mu$ s;  $\delta$  = 0.02.

# THERMAL CHARACTERISTICS

| SYMBOL               | PARAMETER                                   | CONDITIONS | VALUE | UNIT |
|----------------------|---|------------|-------|------|
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient | note 1     | 220   | K/W  |
|                      |   | note 2     | 180   | K/W  |

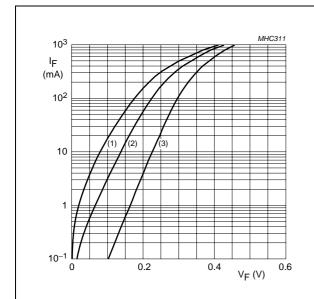
# **Notes**

- 1. Device mounted on an FR4 printed-circuit board with Cu clad 10 x 10 mm.
- 2. Device mounted on an FR4 printed-circuit board with Cu clad 40 x 40 mm.

# Low V<sub>F</sub> (MEGA) Schottky barrier diode

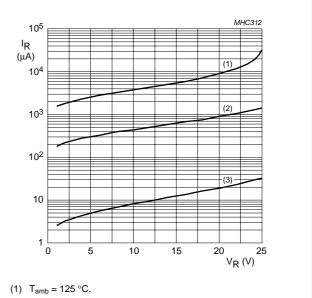
# PMEG2010EA

# **GRAPHICAL DATA**



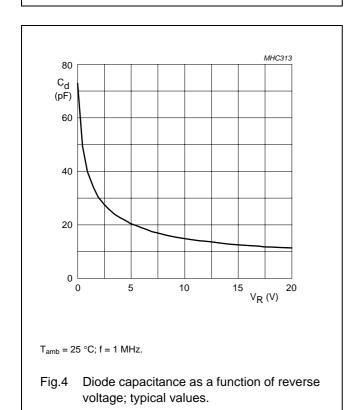
- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.2 Forward current as a function of forward voltage; typical values.



- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \,^{\circ}C$ .

Fig.3 Reverse current as a function of reverse voltage; typical values.



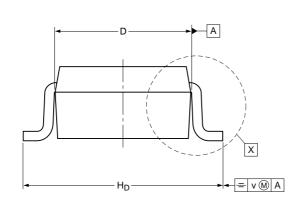
# Low V<sub>F</sub> (MEGA) Schottky barrier diode

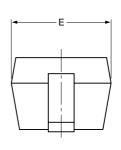
# PMEG2010EA

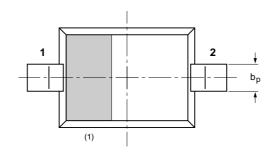
# **PACKAGE OUTLINE**

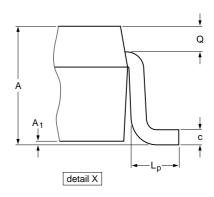
Plastic surface-mounted package; 2 leads

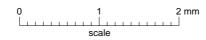
SOD323











# DIMENSIONS (mm are the original dimensions)

| UNIT | Α          | A <sub>1</sub><br>max | bp           | С            | D          | E            | H <sub>D</sub> | Lp           | Q            | v   |
|------|------------|-----------------------|--------------|--------------|------------|--------------|----------------|--------------|--------------|-----|
| mm   | 1.1<br>0.8 | 0.05                  | 0.40<br>0.25 | 0.25<br>0.10 | 1.8<br>1.6 | 1.35<br>1.15 | 2.7<br>2.3     | 0.45<br>0.15 | 0.25<br>0.15 | 0.2 |

#### Note

The marking bar indicates the cathode

| OUTLINE | REFERENCES |       |       |  | EUROPEAN   | ISSUE DATE                      |
|---------|------------|-------|-------|--|------------|---------------------------------|
| VERSION | IEC        | JEDEC | JEITA |  | PROJECTION | ISSUE DATE                      |
| SOD323  |            |       | SC-76 |  |            | <del>03-12-17</del><br>06-03-16 |

# Low V<sub>F</sub> (MEGA) Schottky barrier diode

# PMEG2010EA

#### **DATA SHEET STATUS**

| DOCUMENT<br>STATUS <sup>(1)</sup> | PRODUCT<br>STATUS <sup>(2)</sup> | DEFINITION  |
|-----------------------------------|----------------------------------|---|
| Objective data sheet              | Development                      | This document contains data from the objective specification for product development. |
| Preliminary data sheet            | Qualification                    | This document contains data from the preliminary specification.                       |
| Product data sheet                | Production                       | This document contains the product specification.                                     |

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Printed in The Netherlands R76/02/pp7 Date of release: 2004 Feb 06 Document order number: 9397 750 12626

